查询MPS4355供应商 捷多邦，专业PCB打样工厂，24小时加急出货

MICRO ELECTRONICS

PNP SILICON TRANSISTOR

DESCRIPTION

MPS4355 is PNP silicon planar epitaxial transistor designed for AF medium power amplifiers.

TO-92

EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CEO}	60V
Collector-Emitter Voltage	V_{CBO}	60V
Emitter-Base Voltage	V_{EBO}	5V
Collector Current	I_C	1A
Continuous Power Dissipation	P_d	625mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS	
Collector-Base Breakdown Voltage	BVCBO	60		V	IC=10μA	IE=0
Collector-Emitter Breakdown Voltage	LVCEO	60		V	IC=10mA	IB=0*
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA	IC=0
Collector Cutoff Current	ICES		50	nA	VCB=50V	VEB=0
D.C. Current Gain	HFE	75			IC=500mA	VCE=10V*
		75			IC=100mA	VCE=10V*
		100	400		IC=10mA	VCE=10V
		75			IC=1mA	VCE=10V*
		60			IC=100μA	VCE=10V

MICRO ELECTRONICS LTD.
38, Hung To Road, Microtron Bulding, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

Oct-96

pdf.dzsc.com

MPS 4355

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS	
Collector-Emitter Saturation Voltage	VCE(sat)		0.15	V	IC=150mA	IB=15mA*
			0.9	V	IC=500mA	IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		0.5	V	IC=150mA	IB=15mA*
			1.1	V	IC=500mA	IB=50mA*
Output Capacitance	Cob		30	pF	VCB=10V	f=1MHz
Current Gain-Bandwidth Product	fT	100		MHz	IC=50mA	VCE=10V